TSMC-02-1193

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January 6, 2004

To: Commissioner for Patents P.O.Box 1450 Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572 28 Davis Avenue Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/694,684 10/28/03

Ping-Yi Hsin et al.

METHOD OF FORMING METAL-INSULATOR-METAL (MIM) CAPACITORS AT COPPER PROCESS

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

## CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

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U.S. Patent 6,528,384 to Beckmann et al., "Method for Manufacturing a Trench Capacitor," describes a method for manufacturing a trench capacitor.

U.S. Patent 6,495,874 to Kawamura et al., "Semiconductor Device and Production Process Thereof," describes a semiconductor device and production process thereof.

U.S. Patent 6,384,442 to Chen, "Fabrication Process for Metal-Insulator-Metal Capacitor with Low Gate Resistance," describes a fabrication process for metal-insulator-metal capacitor with low gate resistance.

U.S. Patent 6,346,454 to Sung et al., "Method of Making
Dual Damascene Interconnect Structure and Metal Electrode
Capacitor," describes a method of making dual damascene interconnect structure and metal electrode capacitor.

Sincerely,

Stephen B. Ackerman,

Reg. No. 37761

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## ASSOCIATE POWER OF ATTORNEY

I hereby appoint Stephen G. Stanton, registration number 35,690, as my associate attorney in this case. His telephone number is (610) 296-5194.

Please continue to direct all correspondence in this case to the undersigned attorney.

Respectfully submitted,

Stephen B. Ackerman,

Principal attorney of record